



B.E/B.TECH DEGREE EXAMINATIONS: NOV/DEC 2023

(Regulation 2018)

Fifth Semester

ELECTRICAL AND ELECTRONICS ENGINEERING

U18EEE0005:VLSI Design

COURSE OUTCOMES

- CO1:** Recollect and study the fundamentals of electronics devices and circuits.
CO2: Understand the principle and working of MOS and CMOS device.
CO3: Apply the fundamentals of digital circuits and CMOS technology to develop different design techniques.
CO4: Design various digital modules and systems using different CMOS design techniques.
CO5: Analyse the different CMOS digital modules for performance parameters such as gate size and power.
CO6: Understand the concepts of programmable devices for custom design.

Time: Three Hours

Maximum Marks: 100

Answer all the Questions:-

PART A (10 x 2 = 20 Marks)

(Answer not more than 40 words)

- | | | |
|---|-----|-------------------|
| 1. Differentiate NMOS and PMOS transistors. | CO1 | [K ₂] |
| 2. Write the current equation in saturation mode of MOS characteristics. | CO2 | [K ₂] |
| 3. Write the working of transmission gate with its circuit diagram. | CO3 | [K ₂] |
| 4. Justify why NMOS is preferred for Pull Down network. | CO3 | [K ₄] |
| 5. Draw the circuit diagram for positive edge triggered register element. | CO4 | [K ₃] |
| 6. How many address lines required for 2KB memory? | CO4 | [K ₃] |
| 7. List out few high speed adders | CO5 | [K ₂] |
| 8. Write the advantages of barrel shifter. | CO5 | [K ₂] |
| 9. What is FPGA? | CO6 | [K ₂] |
| 10. List the advantages of semi-custom design. | CO6 | [K ₂] |

Answer any FIVE Questions:-

PART B (5 x 16 = 80 Marks)

(Answer not more than 400 words)

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|--|---|-----|-------------------|
| 11. a) Derive the current equation for MOS device. | 8 | CO1 | [K ₃] |
| b) What are the types of scaling models and scaling factors? Derive scaling factors for 1. Gate area 2. Gate capacitance 3. Gate delay | 8 | CO2 | [K ₃] |

12.	a)	Illustrate how NOR based 4x4 bit ROM can be designed to store following data. 1100; 1110; 0010; 0000;	10	CO4	[K ₅]
	b)	Explain the working of accumulator with suitable clock diagram.	6	CO4	[K ₂]
13.	a)	Describe the types of power dissipation in MOS circuits.	8	CO3	[K ₂]
	b)	Design CMOS and Pseudo NMOS circuit to implement following Boolean function. i) $F' = [(A+B).(C.D)] .(E+G)$	8	CO3	[K ₅]
14.	a)	Design and implement CMOS based 4 bit adder using full adder circuit.	16	CO4	[K ₅]
15.	a)	Explain the working of 4 bit barrel shifter with circuit diagram.	8	CO4	[K ₃]
	b)	Implement the following Boolean equation using RAM based LUT method. $Z = (A'.B) + (C.D)$	8	CO6	[K ₅]
16.	a)	Explain the Gate Array based semi custom design with its types.	8	CO6	[K ₂]
	b)	Illustrate typical Configurable Logic Block with its working and suitable diagram	8	CO6	[K ₂]
